EAST Search History

10/596450

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/596450	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 19:09
L2	56181	FET and (field adj effect adj transistor) and channel and region and source abd drain and gate and spacer and doping and concentration and conductivity implanting and ions and heavy silicon and amorphous and annealing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 19:12
L3	29900	FET and (field adj effect adj transistor) and channel and region and source abd drain and gate and spacer and doping and concentration and conductivity implanting and ions and heavy and silicon and amorphous and annealing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 19:13
L4	29504	FET and (field adj effect adj transistor) and channel and region and source abd drain and gate and spacer and doping and concentration and conductivity implanting and ions and heavy and silicon and amorphous and annealing and (implanting adj heavy adj ions)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 19:13
L5	605	FET and (field adj effect adj transistor) and channel and region and source and drain and gate and spacer and doping and concentration and conductivity implanting and ions and heavy and silicon and amorphous and annealing and (implanting adj heavy adj ions)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 19:14
L6	0	FET and (field adj effect adj transistor) and channel and region and source and drain and gate and spacer and doping and concentration and conductivity and implanting and ions and heavy and silicon and amorphous and annealing and (implanting adj heavy adj ions)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 19:14

EAST Search History

L7	10	FET and (field adj effect adj transistor) and channel and region and source and drain and gate and spacer and doping and concentration and conductivity and implanting and ions and heavy and silicon and amorphous and annealing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 19:17
L8	2	("6432802").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 19:22
L9	1	"6207482".PN.	USPAT; USOCR	OR	OFF	2007/06/27 19:18
L10	1	"6156615".PN.	USPAT; USOCR	OR	OFF	2007/06/27 19:18
L11	1	"6096586".PN.	USPAT; USOCR	OR	OFF	2007/06/27 19:18
L12	1	"6080630".PN.	USPAT; USOCR	OR	OFF	2007/06/27 19:19
L13	1	"6037640".PN.	USPAT; USOCR	OR	OFF	2007/06/27 19:20
L14	1	"5753556".PN.	USPAT; USOCR	OR	OFF	2007/06/27 19:20
L15	1	"5648287".PN.	USPAT; USOCR	OR	OFF	2007/06/27 19:20
L16	1	"4728617".PN.	USPAT; USOCR	OR	OFF	2007/06/27 19:21
L17	1	"4198250".PN.	USPAT; USOCR	OR	OFF	2007/06/27 19:21
L18	2	8 and (semiconductor or device or FET or transistor or field or effect or source or drain or gate or conductivity or type or concentration or region or pocket or heavy or ions or implanting or implantaion or channel or extensions or annealing or heating or body or surface or silicon or amorphous or temperature or inert or RTA or "500" or "650" or "900")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 19:41

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L19		1	12 and (semiconductor or device or FET or transistor or field or effect or source or drain or gate or conductivity or type or concentration or region or pocket or heavy or ions or implanting or implantaion or channel or extensions or annealing or heating or body or surface or silicon or amorphous or temperature or inert or RTA or "500" or "650" or "900")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:27
L20		1	15 and (semiconductor or device or FET or transistor or field or effect or source or drain or gate or conductivity or type or concentration or region or pocket or heavy or ions or implanting or implantaion or channel or extensions or annealing or heating or body or surface or silicon or amorphous or temperature or inert or RTA or "500" or "650" or "900")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 19:59
L21		1	16 and (semiconductor or device or FET or transistor or field or effect or source or drain or gate or conductivity or type or concentration or region or pocket or heavy or ions or implanting or implantaion or channel or extensions or annealing or heating or body or surface or silicon or amorphous or temperature or inert or RTA or "500" or "650" or "900")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:02
L22		1	9 and (semiconductor or device or FET or transistor or field or effect or source or drain or gate or conductivity or type or concentration or region or pocket or heavy or ions or implanting or implantaion or channel or extensions or annealing or heating or body or surface or silicon or amorphous or temperature or inert or RTA or "500" or "650" or "900")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:04
L23		1	10 and (semiconductor or device or FET or transistor or field or effect or source or drain or gate or conductivity or type or concentration or region or pocket or heavy or ions or implanting or implantaion or channel or extensions or annealing or heating or body or surface or silicon or amorphous or temperature or inert or RTA or "500" or "650" or "900")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:08

L24	1	11 and (semiconductor or device or FET or transistor or field or effect or source or drain or gate or conductivity or type or concentration or region or pocket or heavy or ions or implanting or implantaion or channel or extensions or annealing or heating or body or surface or silicon or amorphous or temperature or inert or RTA or "500" or "650" or "900")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:08
L25	3959	438/149	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:28
L26	3581	438/197	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:28
L27	619	438/482	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:28
L28	97	438/495	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:28
L29	37	438/499	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:28
L30	134	438/505	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:29

L31	140	438/506	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:29
L32	149	438/508	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:29
L33	523	438/510	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:29
L34	1092	438/514	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:29
L35	370	438/513	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:29
L36	549	438/663	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:29
L37	1886	438/680	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:29
L38	321	438/733	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:29

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L39	1029	438/734		US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 20:29